Recent Progress in Quantum Dot Laser

Takeo Kageyama\(^1\), Mitsuru Sugawara\(^3\) and Yasuhiko Arakawa\(^1,2\)

\(^1\) Institute for Nano Quantum Information Electronics, The University of Tokyo, 4-6-1 Komaba, Meguro-ku, Tokyo 153-8505, Japan
\(^2\) Institute of Industrial Science, The University of Tokyo, 4-6-1 Komaba, Meguro-ku, Tokyo 153-8505, Japan
\(^3\) QD Laser, Inc. Keihin Bldg. 1F, 1-1 Minamisugawara, Kawasaki-ku, Kawasaki, 210-0855, Japan

Abstract

We present recent progress on quantum dot (QD) lasers mainly focusing on 1.3 \(\mu\)m wavelength range. Historical progress of QD lasers has been promoted by epitaxial improvement to increase QD sheet density to enhance modal gain. Our new approach is to increase spatial QD density by thinning barrier layer in between QD layers by introducing strain engineering and the molecular beam epitaxy (MBE) growth improvement. Small signal modulation analysis of QD lasers exhibited that the modulation bandwidth of the conventional QD laser was limited by long carrier transport time due to the thick active layer, on the other hand, thinner active layer developed in our recent study showed larger and record-high modulation bandwidth up to 13 GHz as 1.3 \(\mu\)m-range QD lasers owing to the reduced carrier transport time.

1. Introduction

Quantum dot (QD) lasers have been attractive light source since its proposal at 1982 [1] not only for telecom/datacom [2] but also for Si-photonics [3] and for extremely-high temperature applications up to 200°C [4] owing to their temperature insensitive characteristics [1][4]. Recently QD lasers have been commercialized [5] using InAs/GaAs QD on GaAs substrate grown by multiple-wafer MBE [6] and fabricated by low cost fab based on DVD lasers. On the other hand, relatively insufficient gain of current QD active media tends to be a limiting factor to extend the variety of devices such as uncooled high-speed DFB lasers. To increase the gain, many researchers have been focusing on increasing “sheet” QD density by modifying epitaxial growth condition of QD layer. On the other hand, we have been focusing on increasing “spatial” QD density by reducing barrier thickness in the multiple stack of QDs, in which barrier thickness had been limited by the large lattice mismatch between InAs and GaAs. We have taken two approaches to reduce barrier layer thickness, one is to reduce average strain by using strain compensation (SC) technology, and the other is the local strain reduction (LSR) at just above buried dot by considering strain coupling through the barrier as a function of buried dot density. Both approaches effectively enabled to reduce the barrier thickness without losing quality of QD active layer, resulting in obtaining higher small signal bandwidth of QD laser owing to the reduction of carrier transport time in QD active layer.

2. Strain Compensation

We have focused on denser stacking of QD layers, which is thought to be a key to increase modal gain without losing the design flexibility, by applying strain-compensation (SC) technique to avoid the accumulation of the average strain. Room-temperature lasing operation of MOCVD-grown SC-QD LD using GaP thin-layer was reported [7], on the other hand, MBE-grown SC-QD LD is limited to all-arsenide materials on InP-substrate [4] probably due to the difficulty in the phosphorous growth in MBE. In this study, we have introduced GaP-SC layers into multiple-stacking of InAs/GaAs quantum dot structure by MBE for the first time. We found that the thickness management is a key to grow flat, tensile-strained GaP layers on GaAs substrate. As shown in Fig. 1, the 0th order peak of the satellite peak in XRD spectra showing the average strain, indicated by arrows in Fig. 1, shifted towards larger diffraction angle by increasing the number of inserted GaP layers on each dot layers. Thus we have confirmed the controllability of the average strain from non-compensation to over-compensation. We obtained first lasing operation for the MBE grown SC-QD LDs on GaAs substrate.

3. Local Strain reduction (LSR) by dot density control

Vertical alignment (VA) between upper and lower dots due to the local strain coupling is known to be a root-cause to compel the barriers to be thick [10], because migrated In-adatoms favor to accumulate into higher strain area during InAs-QD layer growth. Furthermore, VA induces the dot density reduction and dot size inflation (can be seen in Fig. 2), resulting in the peak gain reduction. We have found that higher QD density enables to reduce barrier thickness without increase of VA due to the minimization of local strain just above dot because of strain overlapping from neighboring dots by theoretical and experimental discussions [9], and obtained growth mode map for non-VA and VA as shown in Fig. 2. In this study, we employed 8 QD layer in QD laser structure considering the LSR with increased QD density and reduced barrier thickness respectively as \(6.6 \times 10^{10}\) \(\text{cm}^{-2}\) and 30 nm, which are recognized to be in the edge of no-VA mode, resulting in the total active layer thickness \(L_a\) of 310 nm by simply adjusting the growth temperature of QD layer. The broad-area laser with LSR showed ground-state lasing operation under pulsed injection up to 130°C, which was limited by measurement setup.

4. High Speed Modulation of QD Lasers

QD laser tend to have relatively thick active layer thick-
ness due to the requirement of multiple stack to increase gain and the strain as discussed above. Typical active layer thickness is around 400 nm and thought to increase carrier transport time. We have evaluated the small signal modulation bandwidth for reference QD laser sample with sheet dot density $D = 5.9 \times 10^{10}$ cm$^{-2}$, thinner active layer (310 nm) sample by using GaP-SC with $D = 5.9 \times 10^{10}$ cm$^{-2}$, and also thinner active layer sample obtained by LSR employing with slightly higher QD density of $D = 6.6 \times 10^{10}$ cm$^{-2}$. All samples were grown by MBE and fabricated into standard ridge laser structure with 375 µm × 1.8 µm in size. Rear facet was HR-coated and front facet was as-cleaved.

Fig. 3 shows the small signal responses at 25°C. Record high maximum 3 dB bandwidth $f_{3dB}$ of 13.1 GHz as 1.3 µm-range QD lasers was obtained for LSR sample. GaP-SC sample exhibited $f_{3dB} = 11.0$ GHz, which was higher than the reference sample of $f_{3dB} = 9.5$ GHz but lower than LSR sample in spite of same active layer thickness. To clarify the reason, we analyzed the small signal modulation responses including carrier transport limitation [12][13]. As shown in Fig. 4, $f_{3dB}$ for the reference sample was strongly limited by carrier transport limitation $f_{3dB-trans}$ down to the same level as the relaxation oscillation frequency $f_r$. On the other hand, GaP-SC sample showed almost the same $f_r$ as reference but $f_{3dB}$ extended due to the extension of the transport limitation. Furthermore, LSR sample showed significant $f_r$ extension which might be due to the increased QD density, resulting in significant extension of $f_{3dB}$. These results indicate that not only QD density increase but also the barrier layer reduction is important factor to increase modulation bandwidth. These result indicate that increase in spatial and sheet QD density is the key to boost further the QD laser’s performance.

Fig. 3 Small signal modulation responses of conventional QD laser with active layer thickness $L_{act} = 400$ nm (left), GaP-SC QD laser with $L_{act} = 310$ nm (middle) and LSR QD laser with $L_{act} = 310$ nm (right). Fitting curves are overlaid.

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References